## MA2S357

## Silicon epitaxial planar type

For CATV tuner

## Features

- Large capacitance ratio
- Small series resistance $r_{D}$
- SS-Mini type package, allowing downsizing of equipment and automatic insertion through the taping package

Absolute Maximum Ratings $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Rating | Unit |
| :--- | :---: | :---: | :---: |
| Reverse voltage | $\mathrm{V}_{\mathrm{R}}$ | 34 | V |
| Maximum peak reverse voltage ${ }^{*}$ | $\mathrm{~V}_{\mathrm{RM}}$ | 35 | V |
| Junction temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | $\mathrm{T}_{\mathrm{stg}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Note) $*: \mathrm{R}_{\mathrm{L}}=10 \mathrm{k} \Omega$


Electrical Characteristics $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C} \pm 3^{\circ} \mathrm{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Reverse current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=30 \mathrm{~V}$ |  |  | 10 | nA |
| Diode capacitance | $\mathrm{C}_{\mathrm{D} \text { (0V) }}{ }^{* 1}$ | $\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}, \mathrm{f} \cap \mathrm{MHz}$ | 58.0 |  |  | pF |
|  | $\mathrm{C}_{\mathrm{D}(2 \mathrm{~V})}$ | $\mathrm{V}_{\mathrm{R}}=2 \mathrm{D}, \mathrm{f}=1 \mathrm{MHZ}$ | 29.00 |  | 34.30 |  |
|  | $\mathrm{C}_{\mathrm{D}(25 \mathrm{~V})}$ |  | 2.53 |  | 2.92 |  |
|  | $\mathrm{C}_{\mathrm{D}(10 \mathrm{~V})}$ | $\mathrm{V}_{\mathrm{R}}=10 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | 6.40 |  | 8.32 |  |
|  | $\mathrm{C}_{\mathrm{D}(17 \mathrm{~V},}{ }^{\text {d }}$ | $\mathrm{V}_{\mathrm{R}}=17 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | 3.50 |  | 4.35 |  |
| Capacitance ratio | $\mathrm{C}_{\mathrm{D}(2 \mathrm{~V})} / \mathrm{C}_{\mathrm{D}(25 \mathrm{~V})}$ |  | 11.0 |  |  | - |
| Diode capacitance deviation | 204 | $\mathrm{C}_{\mathrm{D}(2 \mathrm{~V})(10 \mathrm{~V})(17 \mathrm{~V})(25 \mathrm{~V})}$ |  |  | 2.0 | \% |
| Series resistance *2 | $\mathrm{r}_{\mathrm{D}}$ | $\mathrm{C}_{\mathrm{D}}=9 \mathrm{pF}, \mathrm{f}=470 \mathrm{MHz}$ |  |  | 0.54 | $\Omega$ |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.
2. Absolute frequency of input and output is 470 MHz .
3. *1: Measurement at Low signal level
*2: Measuring instrument; YHP MODEL 4191A RF IMPEDANCE ANALYZER


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